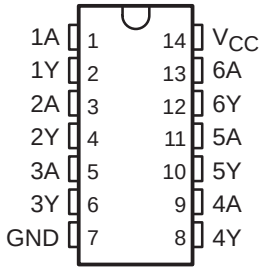
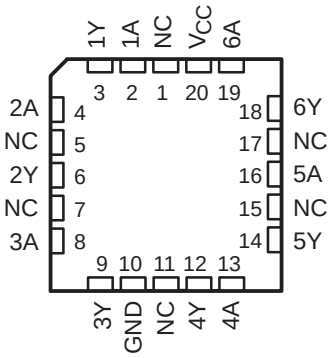
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC}, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC}, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA JESD 17**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs**

SN54LV14 . . . J OR W PACKAGE
SN74LV14 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LV14 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These hex Schmitt-trigger inverters are designed for 2.7-V to 5.5-V V_{CC} operation.

The 'LV14 devices contain six independent inverters. These devices perform the Boolean function $Y = \overline{A}$.

The SN54LV14 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV14 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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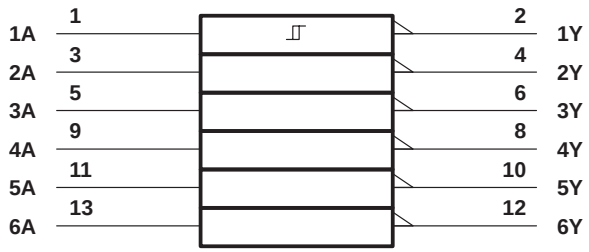
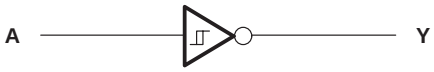
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) . . . . . ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±25 mA
Continuous current through V_{CC} or GND . . . . . ±50 mA
Package thermal impedance, θ_{JA} (see Note 3): D package . . . . . 127°C/W
DB package . . . . . 158°C/W
PW package . . . . . 170°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stressratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV14		SN74LV14		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	5.5	2.7	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2.4		2.4		V
		V_{CC} = 4.5 V to 5.5 V	3.55		3.55		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.4		0.4	V
		V_{CC} = 4.5 V to 5.5 V		1.25		1.25	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V to 3.6 V		–6		–6	mA
		V_{CC} = 4.5 V to 5.5 V		–12		–12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V to 3.6 V		6		6	mA
		V_{CC} = 4.5 V to 5.5 V		12		12	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV14			SN74LV14			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{T+} Positive-going threshold		2.7 V	1		2	1		2	V
		3 V	1.2		2.2	1.2		2.2	
		3.6 V	1.5		2.4	1.5		2.4	
		4.5 V	1.7		3.2	1.7		3.2	
		5.5 V	2.1		3.9	2.1		3.9	
V_{T-} Negative-going threshold		2.7 V	0.4		1.4	0.4		1.4	V
		3 V	0.6		1.5	0.6		1.5	
		3.6 V	0.8		1.8	0.8		1.8	
		4.5 V	0.9		2.25	0.9		2.25	
		5.5 V	1.1		2.75	1.1		2.75	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)		2.7 V	0.3		1.1	0.3		1.1	V
		3 V	0.4		1.2	0.4		1.2	
		3.6 V	0.4		1.2	0.4		1.2	
		4.5 V	0.4		1.4	0.4		1.4	
		5.5 V	0.5		1.5	0.5		1.5	
V_{OH}	I_{OH} = –100 µA	2.7 V to 5.5 V	V_{CC} – 0.2			V_{CC} – 0.2			V
	I_{OH} = –6 mA	3 V	2.4			2.4			
	I_{OH} = –12 mA	4.5 V	3.6			3.6			
V_{OL}	I_{OL} = 100 µA	2.7 V to 5.5 V			0.2			0.2	V
	I_{OL} = 6 mA	3 V			0.4			0.4	
	I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	$V_I = V_{CC}$ or GND	3.6 V			±1			±1	µA
		5.5 V			±1			±1	
I_{CC}	VI = VCC or GND, I_O = 0	3.6 V			20			20	µA
		5.5 V			20			20	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500			500	µA
C_i	$V_I = V_{CC}$ or GND	3.3 V		2.5			2.5		pF
		5 V		3			3		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LV14								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		8	18		12	22		25	ns

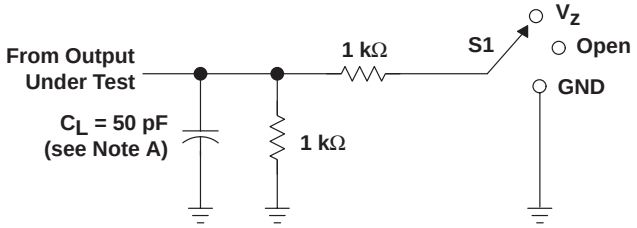
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LV14								UNIT
			V_{CC} = 5 V ± 0.5 V			V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		8	18		12	22		25	ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	3.3 V	22	pF
			5 V	24	

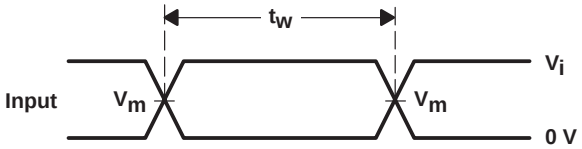
PARAMETER MEASUREMENT INFORMATION



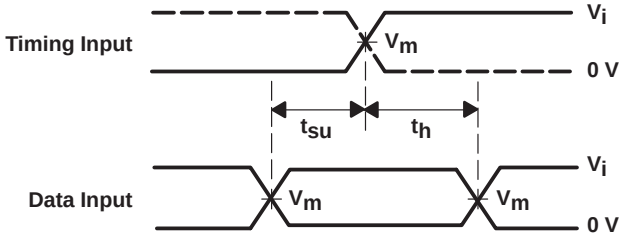
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_z
t_{PHZ}/t_{PZH}	GND

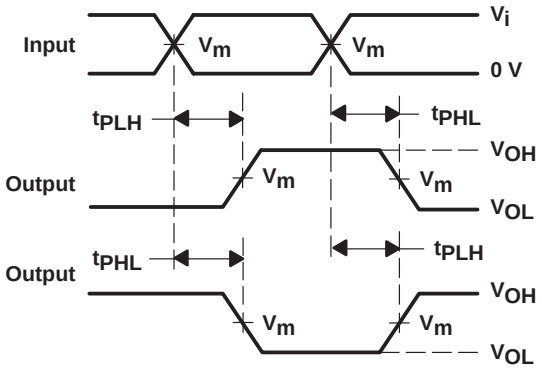
WAVEFORM CONDITION	V_{CC} = 4.5 V to 5.5 V	V_{CC} = 2.7 V to 3.6 V
V_m	$0.5 \times V_{CC}$	1.5 V
V_i	V_{CC}	2.7 V
V_z	$2 \times V_{CC}$	6 V



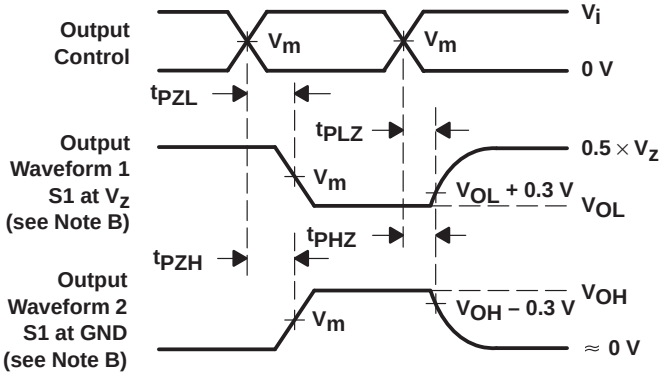
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

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